# **RELIABILITY REPORT**

FOR

# MAX8888EZKxx

# PLASTIC ENCAPSULATED DEVICES

June 24, 2002

# **MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR.

SUNNYVALE, CA 94086

Written by

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#### Conclusion

The MAX8888 successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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## I. Device Description

#### A. General

The MAX8888 low-dropout linear regulator operates from a 2.5V to 5.5V input and delivers up to 300mA continuous (500mA pulsed) current. The MAX8888 includes an open-drain POK ouput flag. The regulator features exceptionally low 100mV dropout at 200mA. This device is available in a variety of preset output voltages in the 1.5V to 3.3V range.

An internal PMOS pass transistor allows the low 55µA supply current to remain independent of load, making this device ideal for portable battery-powered equipment such as personal digital assistants (PDAs), cellular phones, cordless phones, and notebook computers. Other features include a micropower shutdown mode, short-circuit protection, thermal shutdown protection, and an active-low open-drain power-OK (POK) output that indicates when the output is out of regulation. The MAX8888 is available in a thin 5-pin SOT23 package that is only 1mm high.

Rating

# B. Absolute Maximum Ratings

Item

<del></del>
-0.3V to +6.0V
-0.3V  to + (VIN 0.3V)
Continuous
-40°C to +85°C
+150°C
-65°C to +150°C
+300°C
727mW
9.1mW/°C

# II. Manufacturing Information

A. Description/Function: Low-Dropout, 300mA Linear Regulator

B. Process: S8 - Standard 8 micron silicon gate CMOS

C. Number of Device Transistors: 620

D. Fabrication Location: California, USA

E. Assembly Location: Philippines

F. Date of Initial Production: April, 2001

### III. Packaging Information

A. Package Type: 5-Lead SOT

B. Lead Frame: Copper

C. Lead Finish: Solder Plate

D. Die Attach: Silver-filled Epoxy

E. Bondwire: Gold (1.0 mil dia.)

F. Mold Material: Epoxy with silica filler

G. Assembly Diagram: Buildsheet # 05-2301-0084

H. Flammability Rating: Class UL94-V0

I. Classification of Moisture Sensitivity

per JEDEC standard JESD22-A112: Level 1

#### IV. Die Information

A. Dimensions: 59 X 40 mils

B. Passivation: Si<sub>3</sub>N<sub>4</sub>/SiO<sub>2</sub> (Silicon nitride/ Silicon dioxide)

C. Interconnect: TiW/ AlCu/ TiWN

D. Backside Metallization: None

E. Minimum Metal Width: .8 microns (as drawn)

F. Minimum Metal Spacing: .8 microns (as drawn)

G. Bondpad Dimensions: 2.7 mil. Sq.

H. Isolation Dielectric: SiO<sub>2</sub>

I. Die Separation Method: Wafer Saw

#### V. Quality Assurance Information

A. Quality Assurance Contacts: Jim Pedicord (Reliability Lab Manager)

Bryan Preeshl (Executive Director of QA)

Kenneth Huening (Vice President)

B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.

0.1% For all Visual Defects.

C. Observed Outgoing Defect Rate: < 50 ppm

D. Sampling Plan: Mil-Std-105D

#### VI. Reliability Evaluation

#### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4389 \times 80.2}$$
 (Chi square value for MTTF upper limit)
$$\lambda = \frac{1}{192 \times 4389 \times 80.2}$$
 Temperature Acceleration factor assuming an activation energy of 0.8eV
$$\lambda = 13.57 \times 10^{-9}$$
 
$$\lambda = 13.57 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

This low failure rate represents data collected from Maxim's reliability qualification and monitor programs. Maxim also performs weekly Burn-In on samples from production to assure reliability of its processes. The reliability required for lots which receive a burn-in qualification is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on rejects from lots exceeding this level. The Burn-In Schematic (Spec.# 06-5302) shows the static circuit used for this test. Maxim also performs 1000 hour life test monitors quarterly for each process. This data is published in the Product Reliability Report (RR-1M) located on the Maxim website at <a href="http://www.maxim-ic.com">http://www.maxim-ic.com</a>.

#### B. Moisture Resistance Tests

Maxim evaluates pressure pot stress from every assembly process during qualification of each new design. Pressure Pot testing must pass a 20% LTPD for acceptance. Additionally, industry standard 85°C/85%RH or HAST tests are performed quarterly per device/package family.

#### C. E.S.D. and Latch-Up Testing

The MS60-6 die type has been found to have all pins able to withstand a transient pulse of  $\pm 1500$ V, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of  $\pm 250$ mA and/or  $\pm 20$ V.

# **Table 1**Reliability Evaluation Test Results

# MAX8888EZKxx

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Tes	t (Note 1)			
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	80	0
Moisture Testi	ng (Note 2)			
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
Mechanical Str	ress (Note 2)			
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters	77	0

Note 1: Life Test Data may represent plastic D.I.P. qualification lots.

Note 2: Generic process/package data

#### Attachment #3

TABLE II. Pin combination to be tested. 1/2/

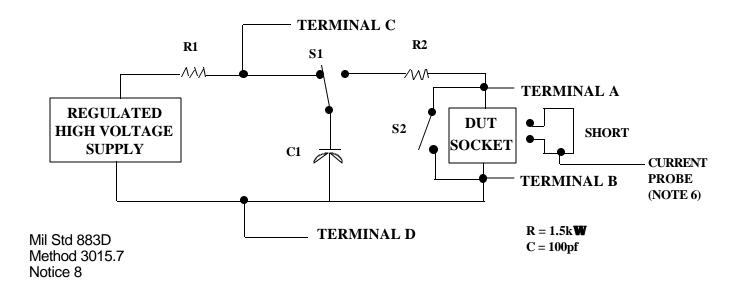
	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V <sub>PS1</sub> 3/	All V <sub>PS1</sub> pins
2.	All input and output pins	All other input-output pins

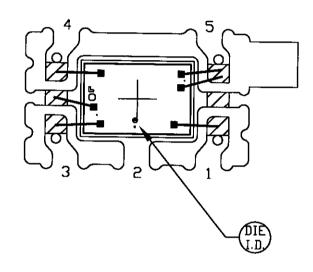
- 1/ Table II is restated in narrative form in 3.4 below.
- 2/ No connects are not to be tested.
- 3/ Repeat pin combination I for each named Power supply and for ground

(e.g., where  $V_{PS1}$  is  $V_{DD}$ ,  $V_{CC}$ ,  $V_{SS}$ ,  $V_{BB}$ , GND,  $+V_{S}$ ,  $-V_{S}$ ,  $V_{REF}$ , etc).

# 3.4 Pin combinations to be tested.

- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., \( \lambda\_{S1} \), or \( \lambda\_{S2} \) or \( \lambda\_{S3} \) or \( \lambda\_{CC1} \), or \( \lambda\_{CC2} \)) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.

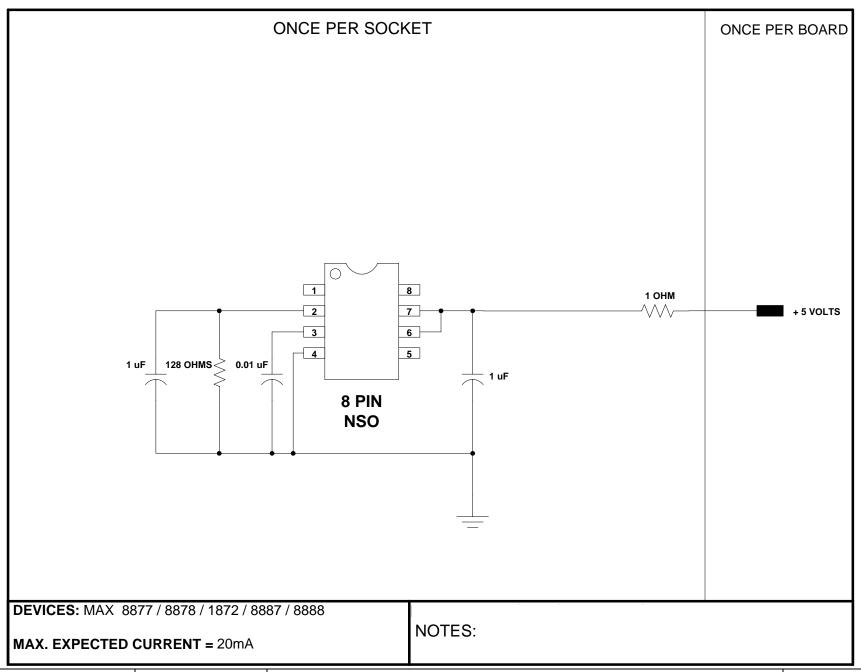




CAVITY DOWN

BONDABLE AREA

PKG. CODE: Z5-1	SIGNATURES		DATE	CONFIDENTIAL & PROPRIE	
	PKG.			BOND DIAGRAM #:	REV:
63×44	DESIGN			05-2301-0084	В



DOCUMENT I.D. 06-5302 REVISION C MAXIMITILE: 883 BI Circuit (MAX 1872/8877/8878/8888) PAGE 2 OF